# 2SB1001

Silicon PNP Epitaxial

# **HITACHI**

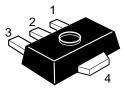
ADE-208-1034 (Z) 1st. Edition Mar. 2001

## Application

- Low frequency power amplifier
- Complementary pair with 2SD1367

#### **Outline**

**UPAK** 



- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector (Flange)



## 2SB1001

### **Absolute Maximum Ratings** $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	-20	V
Collector to emitter voltage	V <sub>CEO</sub>	-16	V
Emitter to base voltage	$V_{EBO}$	-6	V
Collector current	I <sub>c</sub>	-2	A
Collector peak current	i <sub>C(peak)</sub> *1	-3	A
Collector power dissipation	P <sub>c</sub> * <sup>2</sup>	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW ≤ 10 ms, Duty cycle ≤ 20%

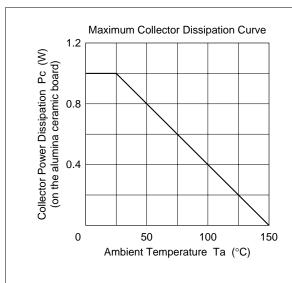
2. Value on the alumina ceramic board (12.5  $\times$  20  $\times$  0.7 mm)

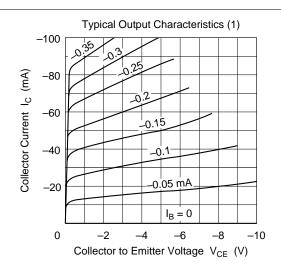
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

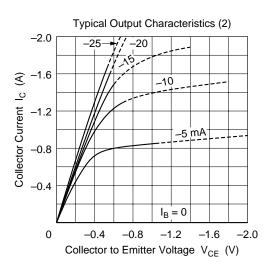
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-20	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-16	_	_	V	$I_{c} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	_	_	V	$I_{E} = -10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-0.1	μΑ	$V_{CB} = -16 \text{ V}, I_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_	_	-0.1	μΑ	$V_{EB} = -5 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	100	_	320		$V_{CE} = -2 \text{ V},$ $I_{C} = -0.1 \text{ A (Pulse test)}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	-0.15	-0.3	V	$I_{c} = -1 \text{ A},$ $I_{B} = -0.1 \text{ A (Pulse test)}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	-1.0	-1.2	V	$I_{c} = -1 \text{ A},$ $I_{B} = -0.1 \text{ A (Pulse test)}$
Gain bandwidth product	f <sub>T</sub>	_	150	_	MHz	$V_{CE} = -2 \text{ V},$ $I_{C} = -10 \text{ mA}$
Collector output capacitance	Cob	_	50	_	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz

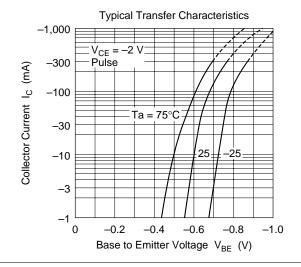
Note: 1. The 2SB1001 is grouped by h<sub>FE</sub> as follows.

Mark	ВН	ВЈ
h <sub>FE</sub>	100 to 200	160 to 320

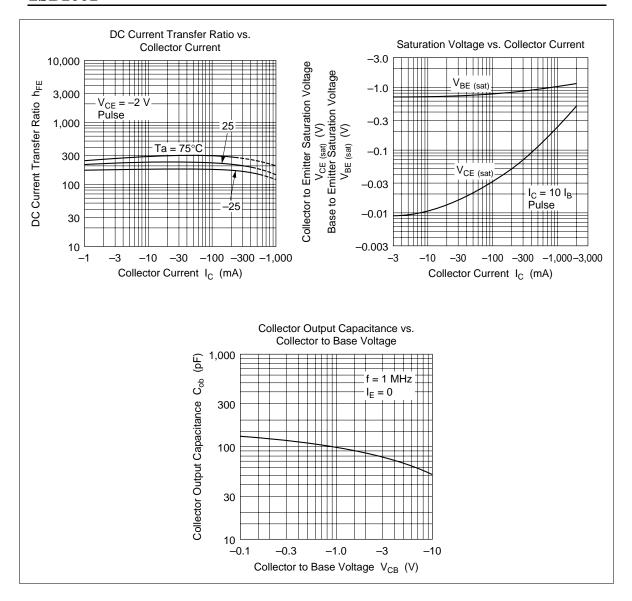




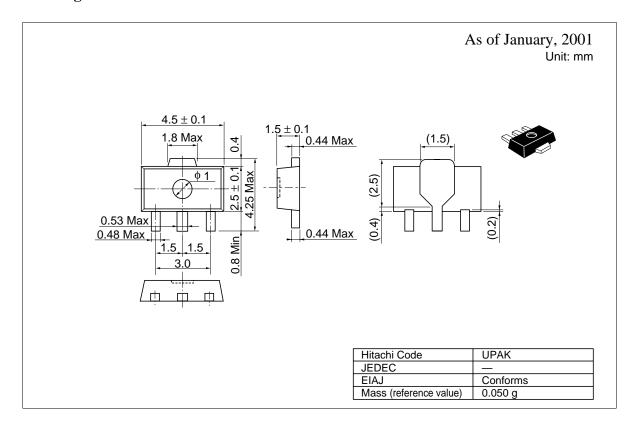




### 2SB1001



### **Package Dimensions**



#### **Cautions**

- 1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
- 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
- 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
- 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as failsafes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
- 5. This product is not designed to be radiation resistant.
- 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
- 7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

# IITAC

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica http://semiconductor.hitachi.com/ Europe http://www.hitachi-eu.com/hel/ecg Asia http://sicapac.hitachi-asia.com Japan http://www.hitachi.co.jp/Sicd/indx.htm

#### For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Germany

Hitachi Europe GmbH Electronic Components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Fax: <1>(408) 433-0223 Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

> Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <886>-(2)-2718-3666 Tel: <44> (1628) 585000 Fax: <44> (1628) 585160

Fax: <65>-538-6933/538-3877 URL: http://www.hitachi.com.sg Hitachi Asia Ltd (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road,

Tel: <65>-538-6533/538-8577

Hung-Kuo Building. Taipei (105), Taiwan Fax: <886>-(2)-2718-8180 Telex: 23222 HAS-TP URL: http://www.hitachi.com.tw Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon, Hong Kong

Tel: <852>-(2)-735-9218 Fax: <852>-(2)-730-0281 URL: http://www.hitachi.com.hk

Copyright © Hitachi, Ltd., 2000. All rights reserved. Printed in Japan. Colophon 2.0

Hitachi Asia Ltd. Hitachi Tower

Singapore 049318

16 Collyer Quay #20-00,